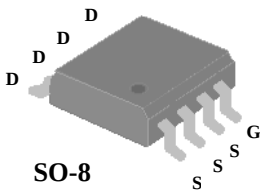
AP4810GSM

RoHS-compliant Product

Advanced Power Electronics Corp.

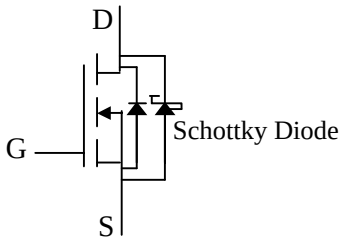
N-CHANNEL MOSFET WITH SCHOTTKY DIODE

- ▼ **Simple Drive Requirement**
- ▼ **Good Recovery Time**
- ▼ **Fast Switching Performance**



SO-8

BV_{DSS}	30V
$R_{DS(ON)}$	13.5mΩ
I_D	11A



Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current[3]	11	A
I_D@T_A=70℃	Continuous Drain Current[3]	9.3	A
I_{DM}	Pulsed Drain Current[1]	50	A
V_{KA}	Schottky Reverse Voltage	30	V
I_F@T_A=25℃	Continous Forward Current	1	A
I_{FM}	Pulsed Diode Forward Current	25	A
P_D@T_A=25℃	Max Power Dissipation (MOSFET)	2.5	W
	Max Power Dissipation (Schottky)	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3](MOSFET)	50	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3](Schottky)	60	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=1mA	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=10A	-	-	13.5	mΩ
		V_{GS}=4.5V, I_D=5A	-	-	20	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=11A	-	18	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V, V_{GS}=0V	-	-	100	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=24V, V_{GS}=0V	-	-	1	mA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=10A	-	14	22.5	nC
Q_{gs}	Gate-Source Charge	V_{DS}=15V	-	3.2	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	8.4	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=15V	-	9	-	ns
t_r	Rise Time	I_D=1A	-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=10V	-	27	-	ns
t_f	Fall Time	R_D=15Ω	-	8	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	1010	1200	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	200	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	170	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Diode+Schottky Forward On Voltage[2]	I_S=1.0A, V_{GS}=0V	-	0.48	0.5	V
I_S	Max Body-Diode+Schottky Continous Current				5	A
t_{rr}	Body Diode+Schottky Reverse Recovery Time	I_S=10A, V_{GS}=0V,	-	21	-	ns
Q_{rr}	Body Diode+Schottky Reverse Recovery Charge	dI/dt=100A/μs	-	13	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board, t ≤10 sec.

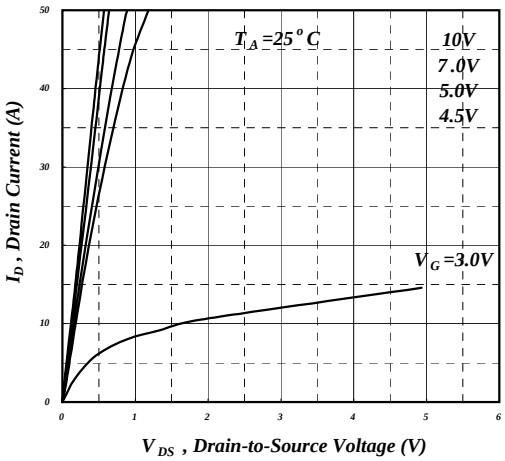


Fig 1. Typical Output Characteristics

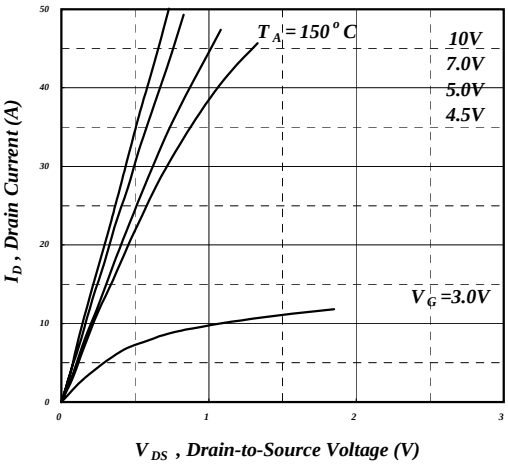


Fig 2. Typical Output Characteristics

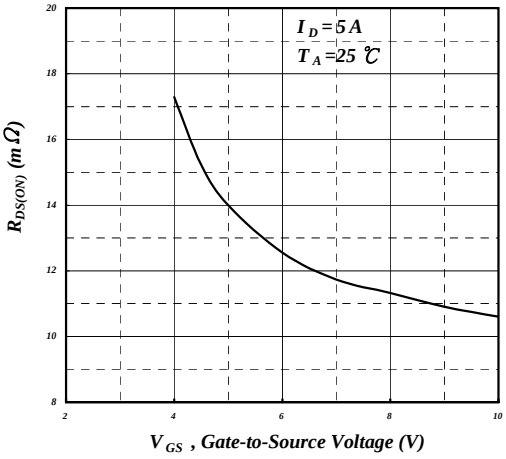


Fig 3. On-Resistance v.s. Gate Voltage

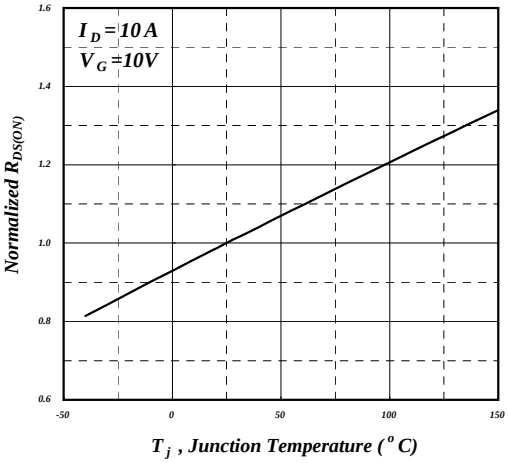


Fig 4. Normalized On-Resistance v.s. Junction Temperature

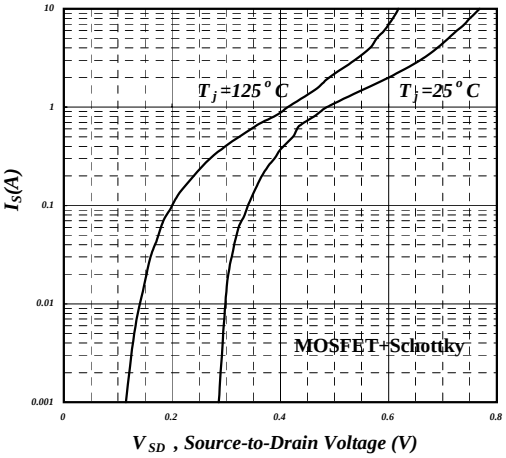


Fig 5. Forward Characteristic of Reverse Diode

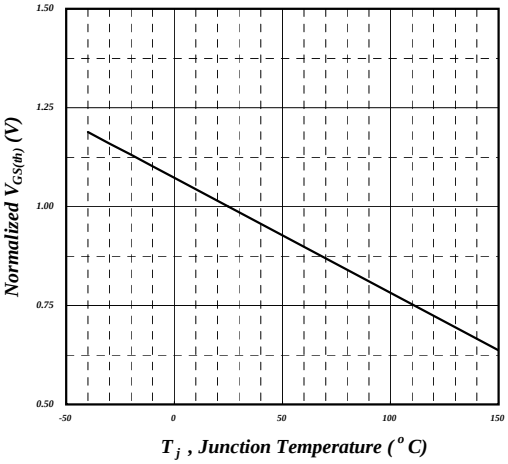


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

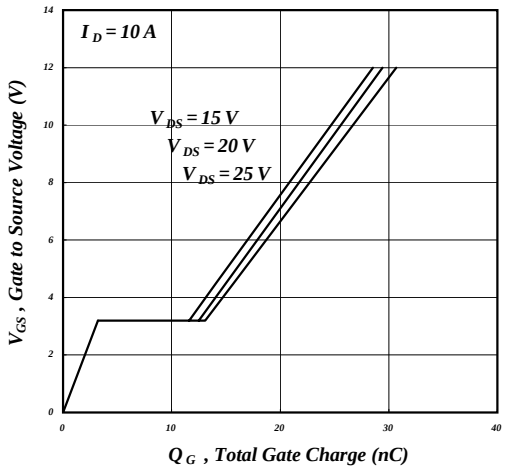


Fig 7. Gate Charge Characteristics

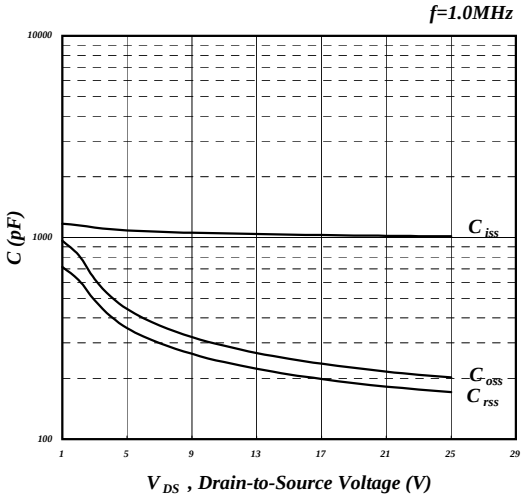


Fig 8. Typical Capacitance Characteristics

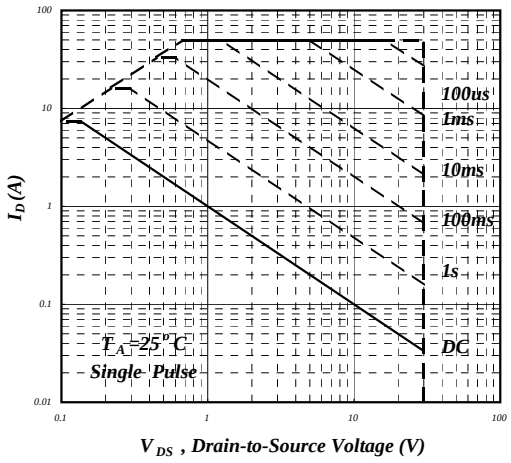


Fig 9. Maximum Safe Operating Area

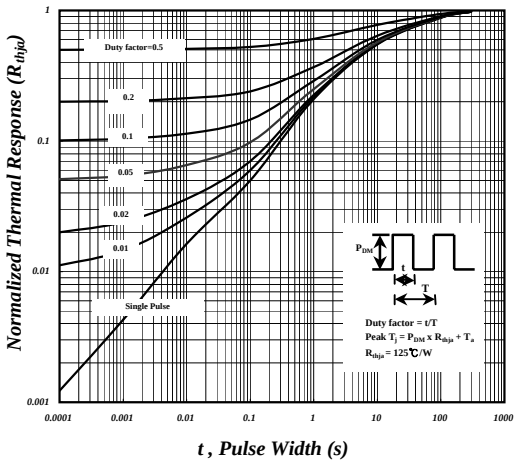


Fig 10. Effective Transient Thermal Impedance

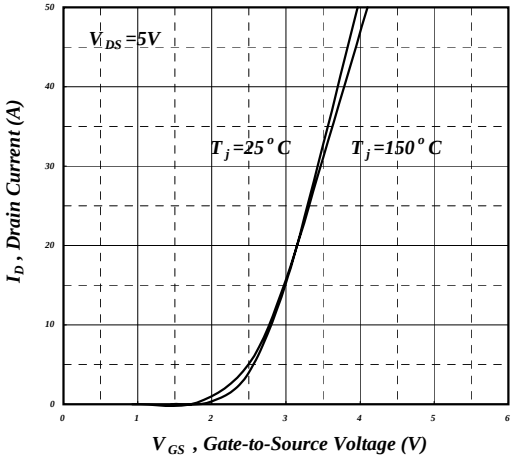


Fig 11. Transfer Characteristics

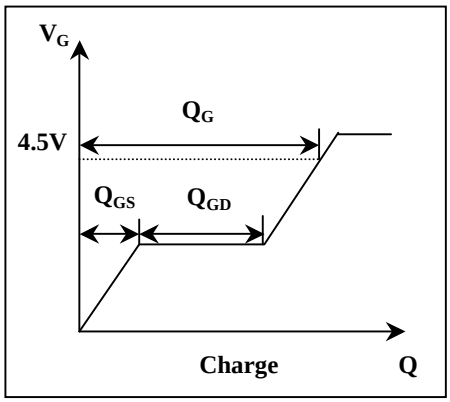


Fig 12. Gate Charge Waveform